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## Supporting materials for

## Ni Nanobelts Induced Enhancement of Hole Transport and Collection for

## High Efficiency and Ambient Stable Mesoscopic Perovskite Solar Cells

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**Fig. S1** FESEM images from the top view of HTM with different Ni nanobelt concentration. (A) 1.2, (B) 1.8, (C) 7.4, and (D) 29.4 mg/mL.



**Fig. S2** *J-V* characteristics of the best performing devices based on different concentration of Ni nanobelts under irradiation of 100 mWcm<sup>-2</sup>, simulated AM1.5 sunlight. All the devices were measured with forward scan with a scan rate of 0.1 V/s. (a) 0 mg/ml, (b) 1.2 mg/ml, (c) 1.8 mg/ml, (d) 7.4 mg/ml, (e) 29.4 mg/ml.

**Table S1** Photovoltaic parameters measured with forward scan for PSCs based on different HTMs at an irradiation of 100 mW cm<sup>-2</sup> AM1.5 sunlight.

HTM	$J_{sc}$ (mA/cm <sup>2</sup> )	$V_{oc}\left(\mathbf{V}\right)$	FF (%)	PCE (%)	$PCE_{average}$ (%) <sup>#</sup>
а	19.48	0.91	61.8	10.95	10.43
b	20.46	0.93	65.7	12.50	12.02
с	21.57	0.93	69.0	13.84	13.43
d	18.82	0.86	57.2	9.26	8.69
e	17.68	0.83	53.6	7.86	7.23

<sup>#</sup>The average values were obtained from five cells.



**Fig. S3** *J-V* characteristic curves of 1.8 mg/ml Ni nanobelts based devices without spiro-OMeTAD interlayer under simulated AM 1.5 sunlight of 100 mW/cm<sup>2</sup> irradiance. The device was measured from forward scan and reverse scan with scan rate of 0.1V/s, respectively.

Table S2 Performance parameters of 1.8 mg/ml Ni nanobelts based device without spiro-OMeTAD interlayer.

Scanning direction	$J_{sc}$ (mA/cm <sup>2</sup> )	$V_{oc}\left(\mathbf{V}\right)$	FF (%)	PCE (%)	$PCE_{average}$ (%) <sup>#</sup>
forward scan	20.95	0.90	58.2	10.97	10.53
reverse scan	21.02	0.99	65.7	13.68	13.22

<sup>#</sup>The average values were obtained from five cells.



Fig. S4 The stabilized power output efficiency ( $PCE_m$ ) values shown as box plots for efficiency distributions of the devices based on 0 and 1.8 mg/mL Ni nanobelts.